

SPICE PARAMETER

QS5U33

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* QS5U33 PMOSFET model
* Date: 2007/03/22
*****D G S
.SUBCKT QS5U33 1 2 3
M1 1 2 3 3 MOS_P
D1 1 3 DREV
.MODEL MOS_P PMOS
+ LEVEL=3
+ L=2.0000E-6
+ W=1
+ KP=11.646E-6
+ RS=10.000E-3
+ RD=62.528E-3
+ VTO=-1.9012
+ RDS=1.0000E6
+ TOX=2.0000E-6
+ CGSO=240.00E-12
+ CGDO=86.257E-12
+ CBD=34.755E-12
+ MJ=.41293
+ RG=2.5
+ N=2
+ RB=1.0000E-3
+ GAMMA=0
+ KAPPA=0
+ UO=300
.MODEL DREV D
+ IS=1.2968E-12
+ N=1.0149
+ RS=.12921
+ IKF=.1155
+ BV=30
+ IBV=1.0000E-6
.ENDS QS5U33

* DQS5U33 D model
* Date: 2007/03/22
* Schottky barrier Diode
.MODEL DQS5U33 D
+ IS=8.9793E-6
+ N=1.0351
+ RS=.10796
+ IKF=2.1946
+ XTI=2
+ EG=.64
+ CJO=92.845E-12
+ M=.4134
+ VJ=.75
+ ISR=4.0000E-6
+ BV=25
+ IBV=1.0000E-6
+ TT=22.937E-9
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